

OSADA et al.  
Appln. No. 10/540,514  
Preliminary Amendment

**AMENDMENTS TO THE SPECIFICATION**

**Please replace the paragraph bridging pages 4 and 5 of the present specification  
with the following amended paragraph:**

A limit value of a thickness of the strain crystal layer in the above described lattice misfit material are given as a function of the strain crystal layer composition, and as for an InGaAs layer with respect to a GaAs layer for example, a Matthews' theoretical equation disclosed in J. Crystal Growth, 27 (1974) p.118 and in J. Crystal Growth, 32 (1974)(1976) p.265, is known, and this theoretical equation has been found to be experimentally correct as a whole.